Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2196	((silicon or ("Si")) adj substrate) with ((SiGe) or ((silicon or ("Si")) adj (germanium or ("Ge"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:36
S2	37	((silicon or ("Si")) adj substrate) with (((SiGe) or ((silicon or ("Si")) adj (germanium or ("Ge")))) adj (layer or film)) with (dop$6 or implant$6) with (hydrogen or ("H. sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 07:59
S3	1	((silicon or ("Si")) adj substrate) with (((SiGe) or ((silicon or ("Si")) adj (germanium or ("Ge")))) adj (layer or film)) with (dop$6 or implant$6) with (hydrogen or ("H. sub.2")) with (anneal$6) with ((silicon or ("si")) adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 14:56
S4	3	(("6464780") or ("6562703") or ("20030143783")).PN.	US-PGPUB; USPAT	OR	OFF	2005/12/08 10:33
S5	181	(438/602).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:38
S6	46	((silicon or ("Si")) adj substrate) with (((("SiGe") or ((silicon or ("Si")) adj (germanium or ("Ge")))) adj (layer or film)) with (dop$6 or implant$6) with (hydrogen or ("H.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 08:00
S7	18	((silicon or ("Si")) adj substrate) with (((("SiGe") or ((silicon or ("Si")) adj (germanium or ("Ge")))) adj (layer or film)) with (dop$6 or implant$6) with (hydrogen or ("H.sub.2")) with anneal$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 12:40
S8	3	(("6562703") or ("6746902") or ("20030140844")).PN.	US-PGPUB; USPAT	OR	OFF	2005/12/07 08:15
S9	0	(((silicon or ("Si")) adj substrate) with (((("SiGe") or ((silicon or ("Si")) adj (germanium or ("Ge")))) adj (layer or film)) with (dop$6 or implant$6) with (hydrogen or ("H.sub.2")) with anneal$4).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 12:40

S10	0	(((silicon or ("Si")) adj substrate) with ((("SiGe") or ((silicon or ("Si")) adj (germanium or ("Ge")))) adj (layer or film)) with (dop$6 or implant$6) with (hydrogen or ("H.sub.2")) with anneal$4).clm.	US-PGPUB	OR	ON	2005/12/07 12:41
S11	1540	(438/149).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 12:41
S13	238	(438/517).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 12:42
S16	571	(438/486).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 13:27
S17	101	(438/518).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 12:42
S20	118	(438/520).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 12:43
S21	196	(438/602).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 12:43
S22	269	(438/933).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 12:43

S23	326	(438/667).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 12:43
S24	216	(438/483).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 12:44
S25	96	(438/501).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 12:44
S26	100	(438/502).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 12:44
S28	224	(438/604).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 12:46
S38	1113	(438/479).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 13:17
S39	811	(438/482).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 13:26
S45	949	(438/48).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/07 13:58
S47	6	(("5879459") or ("6118167") or ("6177307") or ("6326282") or ("6391803") or ("6461937")).PN.	US-PGPUB; USPAT	OR	OFF	2005/12/07 14:16

S50	1	("6326678").PN.	US-PGPUB; USPAT	OR	OFF	2005/12/07 14:38
S51	28	(semiconductor adj substrate) with (trench) with liner with ((atomic adj layer deposition) or ("ALD"))	US-PGPUB; USPAT	OR	ON	2005/12/07 14:43
S53	14	S51 and @ad<="20001019"	US-PGPUB; USPAT	OR	ON	2005/12/07 14:40
S54	93	(semiconductor adj substrate) and ((trench) with liner with ((atomic adj layer deposition) or ("ALD"))) and @ad<="20001019"	US-PGPUB; USPAT	OR	ON	2005/12/07 14:44
S55	90	(semiconductor adj substrate) and ((trench) with liner with ((atomic adj layer deposition) or ("ALD"))) and @ad<="20001019"	USPAT	OR	ON	2005/12/07 14:44
S56	1	("6617635").PN.	US-PGPUB; USPAT	OR	OFF	2005/12/08 10:54
S57	2214	(438/305).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 10:55
S58	739	(438/522).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 10:55
S59	526	(438/478).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 10:56